

ABSTRACT OF THE DISCLOSURE:

A substrate for a semiconductor device includes a crystalline silicon substrate; an insulative silicon compound layer thereon and a 5 crystalline insulation layer on the insulative silicon compound layer, wherein the insulative silicon compound layer contains not more than 10at% of component element of a material constituting the crystalline insulation layer, the component element 10 being provided in the insulative silicon compound layer by diffusion.

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